Application/Control Number: 09/938,435

Art Unit: 1773

5. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Robert Stern on 2/16/05.

The application has been amended as follows:

Non-elected Claims 75 and 77-83 have been cancelled.

6. The following is an examiner's statement of reasons for allowance: The closest prior art Goto et al teaches deposition of TEOS oxide using pulsed RF plasma wherein a TEOS precursor is deposited on a silicon dioxide substrate using a PECVD process to produce an organosilicate film on the substrate such that the thickness uniformity of the film is less than 10% and wherein the process includes inputting He, Oxygen and TEOS into a PECVD chamber and applying RF energy to generate a plasma utilizing standard TEOS conditions wherein He is supplied at 100 sccm, Oxygen at 350 sccm, and TEOS at 185 sccm, at a temperature of 400°C. However, as previously stated by the Applicant, Goto et al was commonly owned and assigned to the same entity as the instant invention at the time of the invention and hence has been disqualified as a prior art reference under 35 U.S.C. 103(c).

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue